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| United States Patent | 12394744                |
| Kind Code            | B2                      |
| Date of Patent       | August 19, 2025         |
| Inventor(s)          | Takao; Katsuhiko et al. |

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### Semiconductor device

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#### Abstract

A semiconductor device includes: a semiconductor element having a first electrode and a second electrode on a first surface, and a third electrode on a second surface, wherein continuity between the second electrode and the third electrode is controlled by a voltage applied to the first electrode; a conductive first lead that is electrically connected to the first electrode and extends beyond a periphery of the first surface; and a conductive second lead that is electrically connected to the second electrode and extends beyond the periphery of the first surface. At least one edge of the periphery of the first surface faces neither the first lead nor the second lead, and portions of the first lead and the second lead that face the periphery of the first surface are provided with respective grooves.

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| <b>Appl. No.:</b>            | <b>17/997823</b>   |
| <b>Filed (or PCT Filed):</b> | <b>July 13, 2020</b>   |
| <b>PCT No.:</b>              | <b>PCT/JP2020/027300</b>   |
| <b>PCT Pub. No.:</b>         | <b>WO2021/225006</b>   |
| <b>PCT Pub. Date:</b>        | <b>November 11, 2021</b>   |

#### Prior Publication Data

|                            |                         |
|----------------------------|-------------------------|
| <b>Document Identifier</b> | <b>Publication Date</b> |
| US 20230187405 A1          | Jun. 15, 2023           |

#### Foreign Application Priority Data

**Publication Classification****Int. Cl.:** H01L23/00 (20060101); H01L23/31 (20060101); H01L23/495 (20060101)**U.S. Cl.:****CPC** H01L24/40 (20130101); H01L23/3107 (20130101); H01L23/49562 (20130101); H01L24/16 (20130101); H01L24/73 (20130101); H01L2224/1601 (20130101); H01L2224/16245 (20130101); H01L2224/40245 (20130101); H01L2224/73255 (20130101); H01L2924/13091 (20130101)**Field of Classification Search****CPC:** H01L (24/40)**USPC:** 257/666

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## Background/Summary

### RELATED APPLICATIONS

(1) The present application is a National Phase of International Application Number PCT/JP2020/027300 filed Jul. 13, 2020, which claims the benefit of priority from Japanese Patent Application No. 2020-082299, filed on May 8, 2020.

### TECHNICAL FIELD

(2) The present invention relates to a semiconductor device.

### BACKGROUND ART

(3) A semiconductor device having a power semiconductor element such as a MOSFET sealed in a package (sealing portion) has been proposed (see Patent Literature 1). Power semiconductor elements such as MOSFETs are expected to be applied as control elements that control high-voltage power.

### CITATION LIST

Patent Literature

(4) Patent Literature 1: U.S. Patent Application Publication No. 2004/0063240 Specification

### SUMMARY

#### Technical Problem

(5) In the power semiconductor elements such as MOSFETs, a high voltage of about 60 to 200 V or more is applied between a gate region (gate electrode) as well as a source region (source electrode) formed on a first surface and a drain region (drain electrode) formed on a second surface, which is the opposite side to the first surface. In addition, almost the same voltage as the voltage applied to the drain region is generated at a periphery of the first surface due to the structure of a MOSFET.

(6) Therefore, when a gate lead connected to the gate region on the first surface and a source lead connected to the source region on the first surface are arranged near the periphery of the first surface of the MOSFET, insulation properties may sometimes be insufficient between the gate lead as well as the source lead and the periphery.

#### Solution to Problem

(7) According to a first aspect, a semiconductor device includes: a semiconductor element having a first electrode and a second electrode on a first surface facing in a first direction, and a third electrode on a second surface facing in an opposite direction to the first direction, wherein continuity between the second electrode and the third electrode is controlled by a voltage applied to the first electrode; a conductive first lead that is electrically connected to the first electrode and extends along the first surface beyond a periphery of the first surface; and a conductive second lead that is electrically connected to the second electrode and extends along the first surface beyond the periphery of the first surface. The periphery of the first surface of the semiconductor element has edges, at least one of which faces neither the first lead nor the second lead, and portions of the first lead and the second lead that face the periphery of the first surface of the semiconductor element are provided with respective grooves.

#### Advantageous Effects of Invention

(8) According to the present invention, it is possible to realize a semiconductor device that is excellent in insulation properties between a first lead as well as a second lead formed along a first surface of a semiconductor element and a periphery of the first surface of the semiconductor element.

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## Description

## BRIEF DESCRIPTION OF DRAWINGS

- (1) FIGS. **1A** and **1B** are views illustrating a schematic configuration of a semiconductor device according to a first embodiment.
- (2) FIG. **2** is a view illustrating a state where the semiconductor device according to the first embodiment is mounted on a wiring substrate.
- (3) FIGS. **3A** and **3B** are views illustrating a schematic configuration of a semiconductor device according to a variation **1**.
- (4) FIG. **4** is a view illustrating a schematic configuration of a semiconductor device according to a variation **2**.

## DESCRIPTION OF EMBODIMENTS

- (5) (Semiconductor Device of First Embodiment)
- (6) A semiconductor device **1** according to a first embodiment will be described below with reference to FIGS. **1A** and **1B**. In FIGS. **1A** and **1B** and subsequent figures, arrows corresponding to the X direction, the Y direction, and the Z direction indicate their respective positive (+) directions. In addition, the X direction, the Y direction, and the Z direction are perpendicular to one another.
- (7) In this specification, the  $-Z$  direction is also referred to as a “first direction” or a “downward direction”. The  $+Z$  direction is also referred to as an “upward direction”, and viewing an object from the upward direction ( $+Z$  direction) is also referred to as a “top view”.
- (8) FIG. **1A** is a view illustrating a top view-state of the semiconductor device **1** according to the first embodiment. FIG. **1B** is a view illustrating an XZ plane cross-sectional view of the semiconductor device **1** along an AA cross-section line in FIG. **1A**. Note that, for easy understanding, FIG. **1B** also shows a part of a second electrode **12** that is not actually on the AA cross-section line, which will be described later.
- (9) FIG. **1A** illustrates an XY plane cross-sectional view of the semiconductor device **1** along a BB cross-section line in FIG. **1B**. Note that, for easy understanding, FIG. **1A** also shows a semiconductor element **10**, a first electrode **11**, and the second electrode **12** that are not actually on the BB cross-section line, which will be described later.
- (10) The semiconductor device **1** includes the semiconductor element **10** sealed with a sealing portion **20**. The semiconductor element **10** is, for example, a metal oxide semiconductor field effect transistor (MOSFET) as a power semiconductor element. The semiconductor element **10** includes the first electrode **11** as a gate electrode, for example, and the second electrode **12** as a source electrode on a first surface **S1** facing in the  $-Z$  direction (first direction), for example. The semiconductor element **10** includes a third electrode **13** as a drain electrode on a second surface **S2** facing in the opposite direction to the first direction, for example.
- (11) Like a general MOSFET, continuity between the second electrode **12** (source electrode) and the third electrode **13** (drain electrode) can be controlled by applying a certain voltage to the first electrode **11** (gate electrode) of the semiconductor element **10**. An internal structure of the semiconductor element **10** is similar to that of a general MOSFET and thus will not be described.
- (12) The shape of the semiconductor element **10** in the top view, that is, the shape of the first surface **S1** in the top view is, for example, rectangular. The first surface **S1** has a periphery defined by four edges **E1** to **E4**. An edge **E1** is on the  $-X$  side of the periphery of the first surface **S1**, an edge **E2** is on the  $-Y$  side of the periphery of the first surface **S1**, an edge **E3** is on the  $+X$  side of the periphery of the first surface **S1**, and an edge **E4** is on the  $+Y$  side of the periphery of the first surface **S1**.
- (13) A first lead **21** made of conductive material is electrically connected to the first electrode **11** on the first surface **S1** of the semiconductor element **10** via a bump **14**. The first lead **21** extends from under (the  $-Z$  side of) the first electrode **11** along the first surface **S1**, that is, while roughly keeping a certain gap from the first surface **S1**, in the  $+X$  direction beyond the edge **E3** constituting the

periphery of the first surface **S1**.

(14) A second lead **22** made of conductive material is electrically connected to the second electrode **12** on the first surface **S1** of the semiconductor element **10** via a bump not shown. The second lead **22** extends from under (the  $-Z$  side of) the second electrode **12** along the first surface **S1** in the  $+X$  direction beyond the edge **E3** constituting the periphery of the first surface **S1**.

(15) The gap between the first surface **S1** of the semiconductor element **10** and the first lead **21** as well as the second lead **22** is roughly equal to the height of the bump **14**, for example, about 0.02 to 0.10 mm.

(16) Meanwhile, as shown in FIG. 1B, a clip portion **23b** is connected to the third electrode **13** on the second surface **S2** of the semiconductor element **10** via a conductive material **15** such as solder or conductive paste. The clip portion **23b** extends from above (the  $+Z$  side of) the third electrode **13** along the second surface **S2** in the  $-X$  direction beyond (to the  $-X$  side from) an edge **E5** constituting a periphery of the second surface **S2**. The clip portion **23b** on the  $-X$  side from the edge **E5** bends toward the  $-Z$  direction and is electrically connected to a base portion **23a** at its tip.

(17) The base portion **23a** and the clip portion **23b** constitute a third lead **23** as a whole. Between an end of the clip portion **23b** and the base portion **23a**, a conductive material not shown may be provided.

(18) The first lead **21**, the second lead **22**, and the third lead **23** are made of conductive material such as metal including copper or the like.

(19) In addition to the semiconductor element **10**, at least parts of the first lead **21**, the second lead **22**, and the third lead **23** is also sealed with the electrically-insulating sealing portion **20**. Note that the first lead **21** has a bottom surface **21B** facing in the first direction ( $-Z$  direction), the second lead **22** has a bottom surface (not shown) facing in the first direction, and the third lead **23** has a bottom surface **23B** facing in the first direction. These bottom surfaces are exposed from the sealing portion **20**.

(20) The first lead **21** has a side surface **21S** facing in the  $+X$  direction, that is, on its far side from the semiconductor element **10**, and the second lead **22** has a side surface **22S** facing in the  $+X$  direction, that is, on its far side from the semiconductor element **10**. These side surfaces are exposed from the sealing portion **20**. The third lead **23** also has a side surface **23S** facing in the  $-X$  direction, that is, on its far side from the semiconductor element **10**, and the side surface is exposed from the sealing portion **20**.

(21) The third lead **23** further has a top surface **23T** on the  $+Z$  side of the clip portion **23b**, and the top surface is exposed from the sealing portion **20**.

(22) In the semiconductor device **1** according to the first embodiment, the first lead **21** and the second lead **22** are positioned to face only one edge **E3** out of the edges **E1** to **E4** constituting the periphery of the first surface **S1** of the semiconductor element **10**. Conversely, three edges **E1**, **E2**, and **E4** out of the edges **E1** to **E4** constituting the periphery of the first surface **S1** of the semiconductor element **10** face neither the first lead **21** nor the second lead **22**.

(23) Furthermore, a portion of the first lead **21** that faces the periphery (edge **E3**) of the first surface **S1** of the semiconductor element **10** is provided with a groove **G1**, and a portion of the second lead **22** that faces the periphery (edge **E3**) of the first surface **S1** of the semiconductor element **10** is provided with a groove **G2**. The groove **G1** increases the gap between the edge **E3** of the first surface **S1** and the first lead **21** to improve the insulation properties between the edge **E3** and the first lead **21**. The groove **G2** increases the gap between the edge **E3** of the first surface **S1** and the second lead **22** to improve the insulation properties between the edge **E3** and the second lead **22**.

(24) Cross-sectional shapes of the grooves **G1** and **G2** on the  $XZ$  plane are not limited to a rectangle as illustrated in FIG. 1B, and may be such a trapezoid that a top of the groove is longer than a bottom of the groove, such a triangle that the groove has a V-shaped bottom, or roughly such a semicircle that the groove has a U-shaped bottom.

(25) The first lead **21** and the second lead **22** has a thickness **T** of about 0.1 to 0.4 mm, for example.

Meanwhile, the grooves G1 and G2 have a depth D of 30% or more and 70% or less of the thickness T described above, for example. When the depth D is 30% or more and 70% or less of the thickness T, it is possible to maintain mechanical stiffness of the first lead **21** and the second lead **22** with the thickness thereof within appropriate bounds, and to improve the insulation properties between the first lead **21** as well as the second lead **22** and the edge E3.

(26) However, if the first lead **21** and the second lead **22** have a sufficiently large thickness T, even when the depth D is smaller than 30% of the thickness T, it is possible to improve the insulation properties between the first lead **21** as well as the second lead **22** and the edge E3. If the first lead **21** and the second lead **33** have a sufficiently large thickness T and have sufficient mechanical stiffness, the depth D may be larger than 70% of the thickness T.

(27) The grooves G1 and G2 have a width W in the X direction (direction in which the first lead **21** and the second lead **22** extend) of about 0.2 to 1 mm, for example.

(28) The center positions in the X direction of the grooves G1 and G2 may be about +40% of the width W or less distant from the position of the edge E3 in the X direction.

(29) In the above-described semiconductor device **1** according to the first embodiment, the three edges E1, E2, and E4 out of the edges E1 to E4 constituting the periphery of the first surface S1 of the semiconductor element **10** face neither the first lead **21** nor the second lead **22**. However, as in several variations described later, at least one of the edges E1 to E4 constituting the periphery of the first surface S1 of the semiconductor element **10** may face neither the first lead **21** nor the second lead **22**.

(30) Also in that case, it is possible to improve the insulation properties between the periphery of the first surface S1 and the first lead **21** as well as the second lead **22** by forming grooves (G1, G2) in portions of the first lead **21** and the second lead **22** that face the periphery (edges E1 to E4) of the first surface S1.

(31) In the above-described semiconductor device **1** according to the first embodiment, the first lead **21** and the second lead **22** extend in the +X direction with respect to the first electrode **11** and the second electrode **12**, respectively, and the third lead **23** (the clip portion **23b**) extends in the -X direction with respect to the third electrode **13**. However, the direction in which the third lead **23** extends is not necessarily opposite to the direction in which the first lead **21** or the second lead **22** extends. For example, the direction in which the third lead **23** extends may be perpendicular to the direction in which the first lead **21** or the second lead **22** extends.

(32) Nevertheless, by setting the direction in which the third lead **23** extends to be opposite to the direction in which the first lead **21** and the second lead **22** extend, it is possible to further improve the insulation properties between the third lead **23**, which is connected to the electrode **13** as the drain electrode, that is, to which a high voltage is applied, and the first lead **21** as well as the second lead **22**, to which a low voltage is applied.

(33) In the semiconductor device **1** according to the first embodiment, the edge E1 of the periphery (edges E1 to E4) of the first surface S1 of the semiconductor element **10** is located in the -X direction in which the third lead **23** extends. The edge E1 faces neither the first lead **21** nor the second lead **22**. That is, neither the first lead **21** nor the second lead **22** extends in the -X direction from the edge E1.

(34) This configuration can increase gaps between the first lead **21** as well as the second lead **22** and the third lead **23** to improve the insulation properties between the first lead **21** as well as the second lead **22** and the third lead **23**. Conversely, the third lead **23** can be arranged near the semiconductor element **10** while keeping at least certain gaps to the first lead **21** and the second lead **22**, allowing for a further reduction in the size in the X direction of the semiconductor device **1**.

(35) Note that the semiconductor device **1** may not necessarily have the third lead **23**. For example, unlike the configuration of the semiconductor device **1**, the electrode **13** as the drain electrode of the semiconductor element **10** may be wired for an electrical connection and, in that case, the

semiconductor device **1** does not require the third lead **23**.

(36) Nevertheless, with the third lead **23**, it is possible to reduce manufacturing cost in a process of mounting the semiconductor device **1**.

(37) The semiconductor device **1** may not necessarily have the sealing portion **20**.

(38) Nevertheless, the sealing portion **20** yields an advantage that the semiconductor device **1** is improved in durability and becomes easy to handle.

(39) The shape of the first surface **S1** of the semiconductor element **10** in the top view is not necessarily a rectangle, and may be a polygon or the like.

(40) In the above description, the second electrode **12** is the source electrode of the MOSFET and the third electrode **13** is the drain electrode of the MOSFET. However, the second electrode **12** may be the drain electrode of the MOSFET and the third electrode **13** may be the source electrode of the MOSFET.

(41) (How Semiconductor Device of First Embodiment is Mounted on Substrate)

(42) FIG. **2** is a cross-sectional view illustrating a state where the semiconductor device **1** according to the first embodiment is mounted on a wiring substrate **30** such as a printed substrate. The semiconductor device **1** is mounted on the wiring substrate **30** in such a way that the first lead **21** and the base portion **23a** of the third lead **23** are mechanically and electrically connected to terminals **31**, **32** formed on the wiring substrate **30** via solder joints **33a**, **33b**, respectively.

(43) Note that the second lead **22** not shown in FIG. **2** is also mechanically and electrically connected to a terminal not shown formed on the wiring substrate **30** via a solder joint not shown. The second lead **22** and the terminal and the solder joint connected to the second lead **22** are hidden by the terminal **31** and the solder joint **33a** in FIG. **2**, and thus are not shown in FIG. **2**.

(44) As described above, in the semiconductor device **1** according to the first embodiment, the first lead **21** and the second lead **22** (see FIGS. **1A** and **1B**) extend beyond (to the +X side from) the periphery (edge **E3**) of the first surface **S1** of the semiconductor element **10**. Thus, in the state of having been mounted on the wiring substrate **30**, at least a part of the solder joint **33a** connected to the first lead **21** can be viewed from the upward direction. The same applies to the solder joint (not shown) connected to the second lead **22**. Therefore, quality of soldering can be easily checked.

(45) Even when the semiconductor device **1** includes the sealing portion **20**, the respective side surfaces **21S**, **22S**, **23S** of the first lead **21**, the second lead **22**, and the third lead **23** on their far sides from the semiconductor element **10** are exposed from the sealing portion **20**. Therefore, as described above, in the state of having been mounted on the wiring substrate **30**, quality of the solder joints **33a**, **33b** connected to the first lead **21**, the second lead **22**, and the third lead **23** can be easily checked.

(46) (Advantageous Effects of Semiconductor Device of First Embodiment)

(47) (1) A semiconductor device **1** according to the first embodiment includes: a semiconductor element **10** having a first electrode **11** and a second electrode **12** on a first surface **S1** facing in a first direction ( $-Z$  direction), and a third electrode **13** on a second surface **S2** facing in an opposite direction to the first direction, wherein continuity between the second electrode **12** and the third electrode **13** is controlled by a voltage applied to the first electrode **11**; a conductive first lead **21** that is electrically connected to the first electrode **11** and extends along the first surface **S1** beyond a periphery (edges **E1** to **E4**) of the first surface **S1**; and a conductive second lead **22** that is electrically connected to the second electrode **12** and extends along the first surface **S1** beyond the periphery (edges **E1** to **E4**) of the first surface **S1**. At least one edge **E1** of the periphery of the first surface **S1** of the semiconductor element **10** faces neither the first lead **21** nor the second lead **21**, and portions of the first lead **21** and the second lead **22** that face the periphery (edges **E2** to **E4**) of the first surface **S1** of the semiconductor element **10** are provided with respective grooves.

(48) With this configuration, it is possible to realize the semiconductor device **1** that is excellent in the insulation properties between the first lead **21** as well as the second lead **22** formed along the first surface **S1** of the semiconductor element **10** and the periphery (edges **E1** to **E4**) of the first

surface **S1** of the semiconductor element **10**.

(49) In the conventional semiconductor device disclosed in Patent Literature 1, a bump or an electrode post connecting a semiconductor element and a lead may be thickened in order to improve insulation properties between the semiconductor element and the lead, which would cause a high resistance value and an increase in the size of the semiconductor device.

(50) Meanwhile, in the above-described semiconductor device **1** according to the first embodiment, it is possible to improve the insulation properties between the semiconductor element **10** and the first lead **21** as well as the second lead **22** without increasing an electrical resistance between the semiconductor element and the leads and without increasing the size of the semiconductor device **1**

(51) The following variations also fall within the scope of the present invention. One or more of the variations can also be combined with the above-described embodiment.

(52) (Semiconductor Device of Variation 1)

(53) A semiconductor device **1a** according to a variation **1** will be described with reference to FIGS. 3A and 3B. Note that a most part of a configuration of the semiconductor device **1a** according to the variation **1** is common to the above-described semiconductor device **1** according to the first embodiment. Thus, differences between them will be mainly described below, and common components are denoted by the same reference symbols and will not be described as appropriate.

(54) FIG. 3A is a view illustrating a top-view state of the semiconductor device **1a** according to the variation **1**. FIG. 3B is a view illustrating an XZ plane cross-sectional view of the semiconductor device **1a** along an AA cross-section line in FIG. 3A. FIG. 3A illustrates an XY plane cross-sectional view of the semiconductor device **1a** along a BB cross-section line in FIG. 3B. As in FIGS. 1A and 1B described above, for easy understanding, FIG. 3A shows a part of a component that is not actually on the BB cross-section line, and FIG. 3B shows a part of a component that is not actually on the AA cross-section line.

(55) Also in the semiconductor device **1a** according to the variation **1**, the first lead **21** extends from under (the  $-Z$  side of) the first electrode **11** along the first surface **S1** in the  $+X$  direction beyond the edge **E3**, which is a part of the periphery of the first surface **S1** located in the  $+X$  direction. Moreover, the first lead **21** also extends from under the first electrode **11** along the first surface **S1** in the  $-X$  direction beyond the edge **E1**, which is a part of the periphery of the first surface **S1** located in the  $-X$  direction.

(56) The second lead **22** also extends from under the second electrode **12** along the first surface **S1** beyond the edge **E3**, which is a part of the periphery of the first surface **S1** located in the  $+X$  direction, and beyond the edge **E1**, which is a part of the periphery of the first surface **S1** located in the  $-X$  direction. Furthermore, the second lead **22** extends beyond the edge **E4**, which is a part of the periphery of the first surface **S1** located in the  $+Y$  direction.

(57) Also in the semiconductor device **1a** according to the variation **1**, one edge **E1** out of the edges **E1** to **E4** constituting the periphery of the first surface **S1** of the semiconductor element **10** faces neither the first lead **21** nor the second lead **22**.

(58) Also in the semiconductor device **1a** according to the variation **1**, portions of the first lead **21** that face edges **E3** and **E1** of the periphery of the first surface **S1** of the semiconductor element **10** are provided with grooves **G1a** and **G1b**, respectively.

(59) In addition, portions of the second lead **22** that face edges **E3**, **E2**, and **E1** of the periphery of the first surface **S1** of the semiconductor element **10** are provided with a groove **G2a** that is continuously formed.

(60) This configuration also results in an improvement in the insulation properties between the periphery (edges **E1** to **E4**) of the first surface **S1** of the semiconductor element **10** and the first lead **21** as well as the second lead **22**.

(61) (Semiconductor Device of Variation 2)

(62) A semiconductor device **1b** according to a variation **2** will be described with reference to FIG.



4. Note that a most part of a configuration of the semiconductor device **1b** according to the variation **2** is common to the above-described semiconductor device **1** according to the first embodiment. Thus, differences between them will be mainly described below, and common components are denoted by the same reference symbols and will not be described as appropriate.

(63) FIG. **4** is a view illustrating a top-view state of the semiconductor device **1b** according to the variation **2**, which corresponds to FIG. **1A** illustrating the semiconductor device **1** according to the first embodiment. An XZ cross-sectional view of the semiconductor device **1b** along an AA cross-section line in FIG. **4** is the same as the XZ cross-sectional view of the semiconductor device **1** according to the first embodiment in FIG. **1B**, and thus is not illustrated.

(64) In the semiconductor device **1b** according to the variation **2**, the width of the second lead **22** in the Y direction is narrower at portions near and beyond the edge **E3** in the +X direction (the edge **E3** is a part of the periphery of the first surface **S1** located in the +X direction) than the width at a portion of the second lead **22** located in the -X direction from the edge **E3**. Thus, the groove **G2** at a portion of the second lead **22** that faces the edge **E3** of the periphery of the first surface **S1** of the semiconductor element **10** is also shorter in the Y direction accordingly than the groove **G2** of the above-described semiconductor device **1** according to the first embodiment.

(65) This configuration also results in an improvement in the insulation properties between the periphery (edges **E1** to **E4**) of the first surface **S1** of the semiconductor element **10** and the first lead **21** as well as the second lead **22**.

(66) Note that the semiconductor device **1b** includes dummy leads **24** between the first lead **21** and the second lead **22** at an end on the +X side. The dummy leads **24** are not electrically connected to any of the first lead **21**, the second lead **22**, the third lead **23**, and the semiconductor element **10**. The dummy leads **24** are provided for preventing cutting force from concentrating on the first lead **21** and the second lead **22** when semiconductor devices **1b** are manufactured, more particularly, a plurality of semiconductor devices **1b** formed side by side on a substrate are cut out from one another.

(67) The various embodiments have been described above, but the present invention is not limited to the details thereof. The embodiments may be utilized individually or in combination thereof. Another mode conceivable within the technical idea of the present invention also falls within the scope of the present invention.

(68) The present application claims the benefit of priority from Japanese Patent Application No. 2020-082299 (filed on May 8, 2020), the content of which is incorporated herein by reference.

## Claims

1. A semiconductor device comprising: a semiconductor element having a first electrode and a second electrode on a first surface facing in a first direction, and a third electrode on a second surface facing in an opposite direction to the first direction, wherein continuity between the second electrode and the third electrode is controlled by a voltage applied to the first electrode; a conductive first lead that is electrically connected to the first electrode via a first conductive bonding material and extends beyond a periphery of the first surface while keeping a certain gap from the first surface; a conductive second lead that is electrically connected to the second electrode via a second conductive bonding material and extends beyond the periphery of the first surface while keeping a certain gap from the first surface; and a conductive third lead that is electrically connected to the third electrode and extends along the second surface beyond a periphery of the second surface, wherein the third lead bends outside the periphery toward the first direction; wherein the periphery of the first surface of the semiconductor element has edges, at least one of which faces neither the first lead nor the second lead, portions of the first lead and the second lead that face the periphery of the first surface of the semiconductor element are provided with respective grooves, the first electrode is formed inside the periphery of the first surface, a

periphery of the first lead, and the groove of the first lead, and the second electrode is formed inside the periphery of the second surface, a periphery of the second lead, and the groove of the second lead.

2. The semiconductor device according to claim 1, wherein a direction in which the third lead extends with respect to the third electrode is opposite to a direction in which the first lead extends with respect to the first electrode or to a direction in which the second lead extends with respect to the second electrode.

3. The semiconductor device according to claim 1, wherein an edge of the periphery of the first surface of the semiconductor element across which the third lead extends faces neither the first lead nor the second lead.

4. The semiconductor device according to claim 1, further comprising an electrically-insulating sealing portion that seals at least parts of the semiconductor element, the first lead, the second lead, and the third lead.

5. The semiconductor device according to claim 4, wherein the first lead and the second lead have respective bottom surfaces on an opposite side to a side facing the first surface of the semiconductor element, the bottom surfaces being on a same plane as a bottom surface of the sealing portion.

6. The semiconductor device according to claim 4, wherein the first lead, the second lead, and the third lead have respective bottom surfaces facing in the first direction, and respective side surfaces facing in a direction perpendicular to the first direction on a far side from the semiconductor element, the bottom surfaces and the side surfaces being exposed from the sealing portion.

7. The semiconductor device according to claim 1, wherein the first lead and the second lead have no bent portions bending toward the first direction.

8. The semiconductor device according to claim 1, wherein the grooves have a depth of 30% or more and 70% or less of a thickness of the first lead and the second lead.

9. The semiconductor device according to claim 1, wherein the first surface has a shape of rectangle.

10. The semiconductor device according to claim 1, wherein the first conductive bonding material is a bump having a height of 0.02 to 0.10 mm.

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